

Dual Channel x1 PCle Redriver/Equalizer

Check for Samples: SN65LVPE501

FEATURES

- Single Lane PCle Equalizer/Redriver
- Support for Both PCle Gen I (2.5Gbps) and Gen II (5.0 Gbps) Speed
- Selectable Equalization, De-emphasis and Output Swing Control
- Integrated Termination
- Hot-Plug Capable
- Receiver Detect
- Low Power:
 - 330mW(TYP), $V_{CC} = 3.3V$
- Auto Low Power Modes:
 - 5mW (TYP) When no Connection Detected
 - 70mW (TYP) When in Auto-Low Power Mode

- Excellent Jitter and Loss Compensation Capability:
 - 30" of 6 mil Stripline on FR4
- Small Foot Print 24 Pin 4 x 4 QFN Package
- High Protection Against ESD Transient

HBM: 3,000 VCDM: 1,500 VMM: 200 V

APPLICATIONS

 PC MB, Docking Stations, Backplane and Cabled Application

DESCRIPTION

The SN65LVPE501 is a dual channel, single lane PCIe redriver and signal conditioner supporting data rates of up to 5.0Gbps. The device complies with PCIe spec revision 2.1.

Programmable EQ, De-Emphasis and Amplitude Swing

The SN65LVPE501 is designed to minimize the signal degradation effects such as crosstalk and inter-symbol interference (ISI) that limits the interconnect distance between two devices. The input stage of each channel offers selectable equalization settings that can be programmed to match loss in the channel. The differential outputs provide selectable de-emphasis to compensate for the anticipated distortion PCIe signal will experience. Level of de-emphasis will depend on the length of interconnect and its characteristics. Both equalization and de-emphasis levels are controlled by the setting of signal control pins EQ1, EQ2 and DE1, DE2.

To provide additional control of signal integrity in extended backplane applications LVPE501 provides independent output amplitude control for each channel. See Table 2 for setting details.

Device PowerOn

Device initiates internal power-on reset after V_{CC} has stabilized. External reset can also be applied at anytime by toggling RST pin. External reset is recommended after every device power-up. When RST is driven high, the device samples the state of EN_RXD, if it is set H device enters Rx.Detect state where each channel will perform Rx.Detect function (as described in PCle spec). If EN_RXD is set L, automatic RX detect function is disabled and both channels are enabled with their termination set to Z_{DC_RX} .

Receiver Detection

While EN_RXD pin is H and device is not in sleep mode (\overline{RST} is H), SN65LVPE501 performs RX.Detect on both channels indefinitely until remote termination is detected on both channels. Automatic Rx detection feature can be forced off by driving EN_RXD low. In this state both channels input termination are set to Z_{DC_RX} .



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DESCRIPTION CONTINUED

Sleep (Shut_Down) Mode

This is low power state triggered by \overline{RST} = L. In sleep mode receiver termination resistor for each of the two channels is switched to $Z_{RX-HIGH_IMP}$ of >50 K Ω and transmitters are pulled to Hi-Z state. Device power is reduced to <1mW (TYP). To get device out of sleep mode \overline{RST} is toggled L-H.

Electrical Idle Support

A link is in an electrical idle state when the TX \pm voltage is held at a steady constant value like the common mode voltage. SN65LVPE501 detects an electrical idle state when RX \pm input voltage of the associated channel falls below V_{EID_TH} min. After detection of an electrical idle state in a given channel the device asserts electrical idle state in its corresponding TX. When RX \pm voltage exceeds V_{EID_TH} max, normal device operation is restored and output starts passing input signal. Electrical idle exit and entry time is specified at \leq 6ns.

Electrical idle support is independent for each channel.

Power Save Features

The device supports three power save modes as described below.

1. Sleep (Shut Down) Mode

This mode can be enabled from any state (Rx detect or active) by driving \overline{RST} L. In this state both channels have their termination set to $Z_{RX-HIGH\ IMP+}$ and outputs are at Hi-Z. Device power is 1mW (MAX)

2. Auto Low Power Mode

This mode is enabled when PS pin is tied H and device is in active mode. In this mode anytime Vin_{diff_pp} falls below selected V_{EID_TH} for a *given channel* and stays below V_{EID_TH} for >1µs (TYP), the associated CH will enter auto low power (ALP) mode where power/CH will be reduced to <1/3rd of normal operating power/CH or about 70mW under typical voltage of 3.3V when ALP conditions are met for both channels. A CH will exit ALP mode whenever Vin_{diff_pp} exceeds max V_{EID_TH} for that channel. Exit latency is 30ns max. To use this mode link latency will need to account for the ALP exit time for N_FTS. ALP mode is handled by each channel independently based on its input differential signal level. This mode can be disabled by leaving PS as NC or tying PS to GND via $4.7k\Omega$.

3. Cable Disconnect Mode

This mode is activated when \overline{RST} is H, $EN_RXD = H$, and no termination is detected by either channel. Device is in the Rx.Detect state whereby it is continuously performing Rx.Detect on both channels. In this state total power consumed by device is typically <3% of normal active power. Or <10mW (MAX).

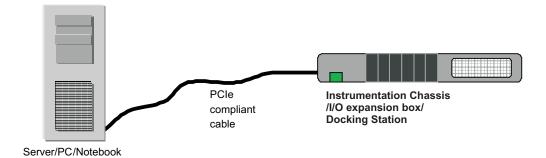
Beacon Support

With its broadband design, the SN65LVPE501 supports low frequency Beacon signal (as defined by PCIe 2.1 spec) used to indicate wake-up event to the system by a downstream device when in L2 power state. All requirements for a beacon signal as specified in PCI Express specification 2.1 must be met for device to pass beacon signals.

Devic Power

The SN65LVPE501 is designed to operate from a single 3.3V supply. Always practice proper supply sequencing procedure. Apply V_{CC} first before any input control pin signals are applied to the device. Power-down sequence is in reverse order.





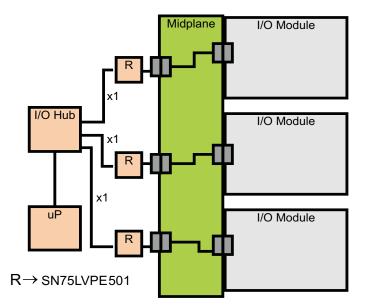


Figure 1. SN65LVPE501 Typical Applications



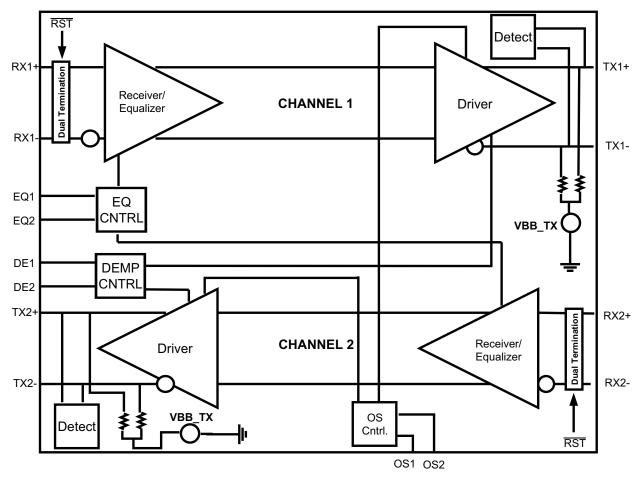
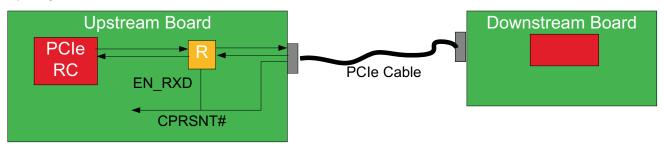


Figure 2. Data Flow Block Diagram

Split System



Enclosed System

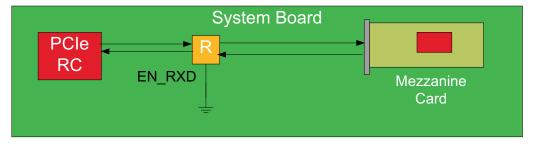


Figure 3. Typical Implementation



Table 1. Pin Description

P	IN					
NUMBER	NAME	I/O TYPE	DESCRIPTION			
HIGH SPEED	DIFFERENTI	AL I/O PINS				
8	RX1+	I, CML				
9	RX1-	I, CML	Non-inverting and inverting CML differential input for CH 1 and CH 2. These pins are tied to an			
20	RX2+	I, CML	internal voltage bias by dual termination resistor circuit.			
19	RX2-	I, CML				
23	TX1+	O, CML				
22	TX1-	O, CML	Non-inverting and inverting CML differential output for CH 1 and CH 2. These pins are			
11 TX2+ O, CML			internally tied to voltage bias by termination resistors.			
12	TX2-	O, CML				
DEVICE CON	TROL PIN ⁽¹⁾	<u> </u>				
5	EN_RXD	I, LVCMOS	Sets device operation modes per Table 2. Internally pulled to VCC			
14	PS	I, LVCMOS	Select auto-low power save mode per Table 2. Internally pulled to GND			
7	RST	I, LVCMOS	Reset device, input active Low. Internally pulled to VCC			
24	RSVD	I, LVCMOS	Reserved for factory test. Must be connected to GND			
SIGNAL CON	TROL PINS ⁽²	2)				
3,16	DE1, DE2	I, LVCMOS	Selects de-emphasis settings for CH 1 and CH 2 per Table 2. Internally tied to V _{CC} /2			
2,17	EQ1, EQ2	I, LVCMOS	Selects equalization settings for CH 1 and CH 2 per Table 2. Internally tied to V _{CC} /2			
4, 15	OS1, OS2	I, LVCMOS	Selects output amplitude for CH 1 and CH 2 per Table 2. Internally tied to V _{CC} /2			
POWER PINS	3	•				
1,13	VCC	Power	Positive supply should be 3.3V ± 10%			
6,10,18,21	GND	Power	Supply ground			

When not used can be left as NC or connected to V_{CC}/GND via $4.7k\Omega$ resistor. Internally biased to $V_{CC}/2$ with >200k Ω pullup/pulldown. When 3-state pins are left as NC board leakage at the pin pad must be <1 μ A otherwise drive to $V_{CC}/2$ to assert mid-level state.

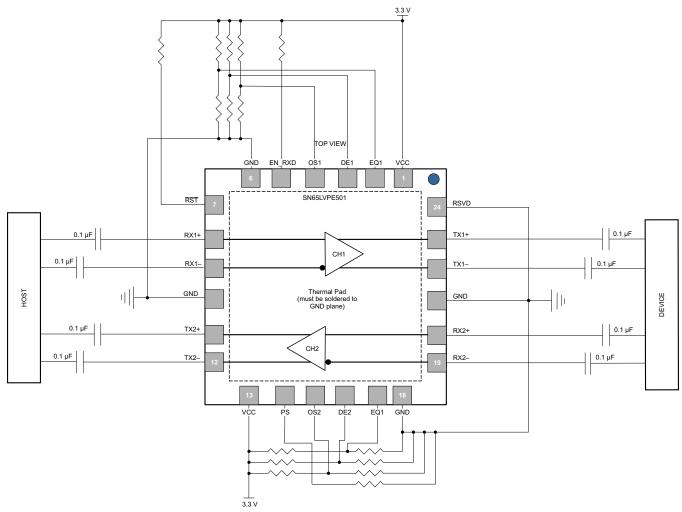


Table 2. Signal Control Pin Setting

0	Sx	TRANSITION BIT AMPLITUDE (TYP mVpp)				
N	IC	1000				
	0	87	75			
	1	11	00			
DEx ⁽¹⁾	OSx ⁽¹⁾ = NC	$OSx^{(1)} = 0$	OSx ⁽¹⁾ = 1			
NC	−3.7 dB	-2.5 dB	-4.6 dB			
0	-6.4 dB	-5.5 dB	-6.6 dB			
1	-9.4 dB	-9.5 dB	-8.7 dB			
EQ	x ⁽¹⁾		ATION dB I Speed)			
N	IC	()			
(0	7				
	1	15				
EN_	RXD	DEVICE FUNCTION				
	0	Set input termination to Z _{DC_RX} and disable Rx. Detect				
	1	Perform Rx.Detect (default, internally pulled to Vcc)				
R	ST	DEVICE FUNCTION				
-	0		scent state and et to Hi-Z			
	1	Device not in shut_down mode (default, internally pulled to Vcc)				
P	'S	DEVICE F	UNCTION			
	0	Auto-low power mode disabled (default, internally pulled to GND				
	1	Auto-low power mode enabled				

⁽¹⁾ Applies to Channel 1 and Channel 2 at 2.5 GHz.





- (1) This is a reference example and it is not intended to represent the best configuration; every designer should select the EQ and DE settings that better fits the system needs. All DEx, EQx and OSx pins default to NC.
- (2) The recommended value for all the resistors shown in the Figure is 4.9K Ω .
- (3) For terminals OSx, DEx, and EQx, populate only pull-up or only pull-down according to the desired setting.

Figure 4. Reference Device Implementation



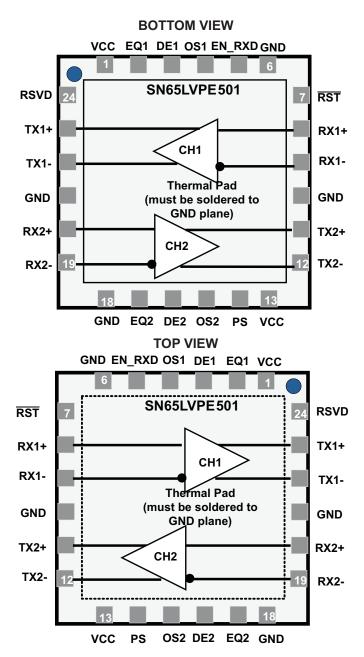


Figure 5. Flow-Through Pin-Out

ORDERING INFORMATION(1)

PART NUMBER	PART MARKING	PCAKAGE
SN65LVPE501RGER	LVPE501	24-pin RGE Reel (large)
SN65LVPE501RGET	LVPE501	24-pin RGE Reel (small)

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.



ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)(1)

		UNIT / VALUES		
Supply Voltage Range (2)	V _{CC}	−0.5 V to 4 V		
Voltage Range	Differential I/O	-0.5V to 4 V		
Vollage Range	Control I/O	-0.5 V to V _{CC} + 0.5		
	(Human Body Model) QSS 009-105 (JESD22-A114B)	±3000 V		
Electrostatic Discharge	(Charged Device Model) QSS 009-147 (JESD22-C101-A)	±1500 V		
	(Machine Model) JESD22-A115-A	±200 V		
Continuous power dissipation	See Thermal Information Table			

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL INFORMATION

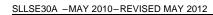
		SN65LVPE501	
	THERMAL METRIC ⁽¹⁾	RGE	UNITS
		24 PINS	
θ_{JA}	Junction-to-ambient thermal resistance ⁽²⁾	46	
$\theta_{\text{JC(TOP)}}$	Junction-to-case(top) thermal resistance (3)	42	
θ_{JB}	Junction-to-board thermal resistance (4)	13	9000
Ψлт	Junction-to-top characterization parameter (5)	0.5	°C/W
ΨЈВ	Junction-to-board characterization parameter (6)	9	
$\theta_{\text{JC(BOTTOM)}}$	Junction-to-case(bottom) thermal resistance (7)	4	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- 7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

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⁽²⁾ All voltage values, except differential voltages, are with respect to network ground terminal.





RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	TYP	MAX	UNIT
V _{CC}	Supply Voltage	3	3.3	3.6	V
C _{COUPLING}	AC Coupling Capacitor	75		200	nF
	Operating free-air temperature	-40		85	°C

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

•	g free-air temperature range (PARAMETER		T CONDITIONS	MIN	TYP	MAX	UNIT
DEVICE BARA				IVIIIV	IIF	IVIAA	UNII
DEVICE PARAI	METERS (under recommended opera		•			ı	
I _{CC}		RST, DEx, EQx, OSx = NC, E $V_{ID} = 1000 \text{mV}_{p-p}$		101	120		
ICC _{idle}	Supply Current	PS=1; When auto-low power	conditions are met		21	26	mA
ICC _{shut-down}		RST = GND			0.2	1	
ICC _{RX.Detect}		\overline{RST} , EN_RXD = NC			2		l
	Maximum Data Rate					5	Gbps
AutoLP _{ENTRY}	Auto Low Power Entry Time	Electrical Idle at Input, Refer t	o Figure 9	1.0	1.3		μs
AutoLP _{EXIT}	Auto Low Power Exit Time	After first signal activity, Refer	to Figure 9		15	30	ns
t _{PU}	Power Up Time	Rx Detect Start Event, Vcc = RST, EN_RXD = H	Stable		15	30	μs
t _{DIS}	Sleep (shut-down) Mode Entry Time	RST H→L; EN_RXD=X				1	μs
T _{ENB}	Sleep (shut-down) Mode Exit Time	RST L→H; EN_RXD=H, Start	of Ex detect event			10	μs
CONTROL LO	GIC (under recommended operating of	conditions, unless otherwise	noted)				
V _{IH}	High level Input Voltage						V
V _{IL}	Low Level Input Voltage		-0.3		0.5	V	
V _{HYS}	Input Hysteresis			150		mV	
	High Level Innut Current	OSx, EQx, DEx = V _{CC}			30		
I _{IH}	High Level Input Current	EN_RXD , $\overline{RST} = V_{CC}$			1	μA	
		OSx, EQx, DEx = GND	-30				
$I_{\rm IL}$	Low Level Input Current	PS = GND	-1			μA	
		EN_RXD , $\overline{RST} = GND$	-20				
RECEIVER AC	/DC (under recommended operating	conditions, unless otherwise	noted)				
Vin _{diff pp}	RX1, RX2 Input Voltage Swing	AC coupled differential signal		100		1200	mVp-p
V _{CM_RX}	RX1, RX2 Common Mode Voltage			0		3.6	٧
Vin _{COM_P}	RX1, RX2 AC Peak common mode voltage					150	mVP
Z _{DC_RX}	DC single ended impedance			40	50	60	Ω
Z _{diff_RX}	DC Differential Input impedance			80	100	120	Ω
Z _{RX_High_IMP+}	DC Input High Impedance	Device in sleep mode Rx term respect to GND over 200mV r	50	74		kΩ	
V _{EID_TH}	Electrical Idle Detect Threshold	Measured at receiver pin (see	65	84	175	mVpp	
		50 MHz – 1.25 GHz		10			dB
RL _{RX-DIFF}	Differential Return Loss	4.05.011 0.5.011	Operating temperature 0°C to 85°C	8			i
		1.25 GHz – 2.5 GHz	Operating temperature –40°C to 85°C	7			dB
RL _{RX-CM}	Common Mode Return Loss	50 MHz – 2.5 GHz	+	10			dB

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ELECTRICAL CHARACTERISTICS (continued)

	free-air temperature range (PARAMETER		ST CONDITIONS	MINI	TVD	MAY	UNIT
TD 4 NO				MIN	TYP	MAX	UNII
TRANSMITTER A	AC/DC (under recommended opera	1	•				
		$R_L = 100\Omega \pm 1\%$, DEx, OS = 1	800	1000	1200		
V_{TXDIFF_PP}		$R_L = 100\Omega \pm 1\%$, DEx = NC, 0			875		mV
		$R_L = 100\Omega \pm 1\%$, DEx = NC, 0	OSx = VCC Transition Bit		1100		
	Differential peak-to-peak Output Voltage	R_L =100 Ω ±1%, DEx=NC, O Non-Transition Bit	Sx = 0,1,NC		655		
V _{TXDIFF_NTB_PP}		R_L =100 Ω ±1%, DEx=0,OSx Non-Transition Bit	= 0,1,NC		495		mV
		R _L =100Ω ±1%, DEx=1, OS> NC Non-Transition Bit	ζ = 0,1,		350		
		DEx, OSx = NC, See	Operating temperature 0°C to 85°C	-3.0	-3.7	-4.0	
	De-Emphasis Level	Figure 11; (for OS1,2 = 1 and 0 see Table 2)	Operating temperature –40°C to 85°C	-3.0	-3.7	-4.2	dB
	·	DEx = 0, OSx = NC			-6.4		
		DEx = 1, OSx = NC			-9.4		dB
T _{DE}	De-Emphasis Width	At 5Gbps			0.8		UI
Z _{diff_TX}	DC Differential Impedance	Defined during signaling		80	100	120	Ω
<u>-αιπ_1 x</u>	Do Billotottiai Impodatioo	Domina during digitaling	Operating temperature 0°C to 85°C	10	100	120	
		f = 50 MHz – 1.25 GHz.	Operating temperature –40°C to 85°C	9.5			
RL_{diff_TX}	Differential Return Loss						dB
		f = 1.25 GHz - 2.5 GHz,	Operating temperature 0°C to 85°C Operating temperature –40°C to 85°C	6			
			5.5				
RL _{CM_TX}	Common Mode Return Loss	f = 50 MHz – 2.5 GHz	10			dB	
I _{TX_SC}	TX short circuit current	TX± shorted to GND		60	90	mA	
V _{TX_CM_DC}	Transmitter DC common-mode voltage	Allowed DC CM voltage at T	2.1	2.65	3.1	V	
V _{TX_CM_AC2}	TX AC common mode voltage at GEN II speed	- May(V. + V.)/2 - Min(V		26	100	mVpp	
V _{TX_CM_AC1}	TX AC common mode voltage at GEN I speed	1012A(Vd+ + Vd-)/2 - 10111(Vd+ +	$Max(V_{d+} + V_{d-})/2 - Min(V_{d+} + V_{d-})/2$				mV
V _{TX_CM_DeltaL0-L0s}	Absolute Delta DC CM voltage during active and idle states	VTX_CM_DC [L0] - VTX_CM_DC [L	_{.0s]} , PS=L	0		100	mV
V _{TX_CM-DC-Line-} Delta	Absolute Delta of DC CM voltage between D+ and D-	V _{TX_CM_DC-D+} [L0] - V _{TX_CM_DC}	C-D- [L0]	0		25	mV
$V_{TX_idle_diff-AC-p}$	Electrical idle differential peak output voltage	$ V_{TX-Idle-D+} - V_{TX-Idle-D-} $ HP fil	tered to remove any DC component	0	1	10	mVpp
$V_{TX_idle_diff\text{-DC}}$	DC Electrical idle differential output voltage	V _{TX_idle-D+} - V _{TX_idle-D-} LP fil	tered to remove any AC component		3.5		mV
V _{detect}	Voltage change to allow receiver detect	Positive voltage to sense rec	ceiver			600	mV
t_R, t_F	Output Rise/Fall time		DEx = NC, OS = NC (CH 0 and CH 1) 20%-80% of differential voltage at the output; VID > 1000mVpp				ps
t _{RF_MM}	Output Rise/Fall time mismatch	DEx = NC, OS = NC (CH 0 a at the output		1	20	ps	
T _{diff_LH} , T _{diff_HL}	Differential Propagation Delay	DEx = NC (CH 0 and CH 1). input and output. See Figure		280	330	ps	
t _{idleEntry} t _{idleExit}	Idle entry and exit times	See Figure 7			4	6	ns
-	ON at GEN II Speed (under recomn	nenced operating conditions)				
	,,	At point A in Figure 10 ⁽²⁾			30	50	
T _{TX-TJ} ⁽¹⁾	Total Jitter	At point B in Figure 10 ⁽²⁾			25	80	ps pp
		At point A in Figure 10 ⁽²⁾			16	30	
					10	55	ps pp

⁽¹⁾ Includes RJ at 10⁻¹²

⁽²⁾ Refer to Figure 10 with ± K28.5 pattern at 5Gbps, -3.5dB DE from source AWG .



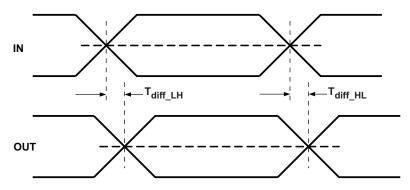


Figure 6. Propagation Delay

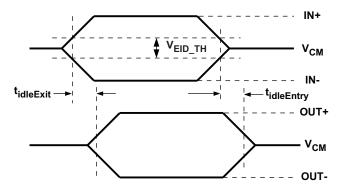


Figure 7. Idle Mode Exit and Entry Delay

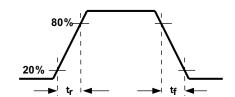


Figure 8. Output Rise and Fall Times

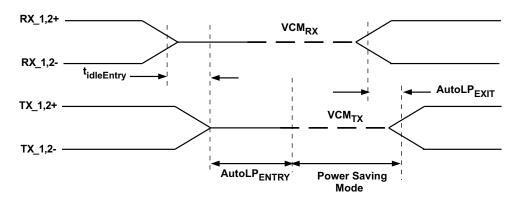


Figure 9. Auto Low Power Mode Timing (when enabled)



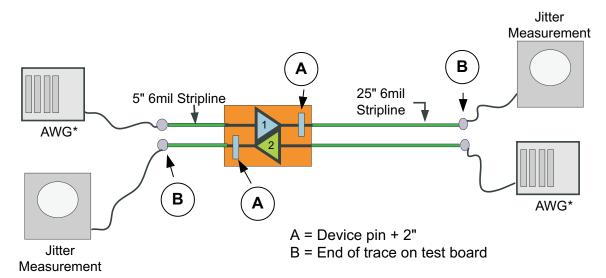


Figure 10. Jitter Measurement Setup

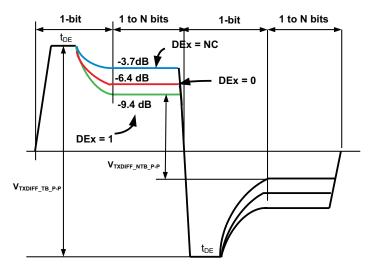


Figure 11. Output De-Emphasis Levels OSx = NC

Typical Eye Diagram and Performance Curves at Output

Input Signal Characteristics: Data Rate = 5 Gbps, V_{ID} = 1000 mVpp, DE = -3.5 dB, Pattern = K28.5 Device Operating Conditions: VCC = 3.3 V, Temp = 25°C Device EQ settings (EQ/DE/OS) adjusted for best eye performance



Output Trace Length Held Constant and Input Trace Length Varied

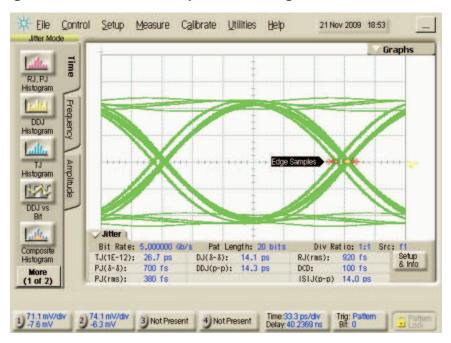


Figure 12. Input Trace = 4 Inches, 6 mil, and Measured at Output Trace = 4 Inches

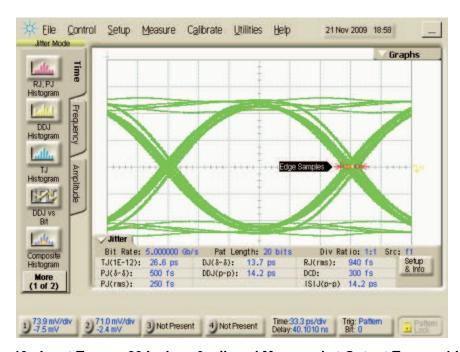


Figure 13. Input Trace = 20 Inches, 6 mil, and Measured at Output Trace = 4 Inches



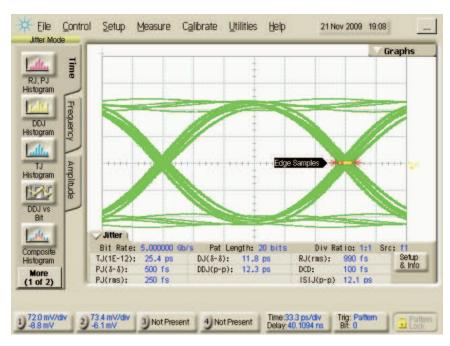


Figure 14. Input Trace = 32 Inches, 6 mil, and Measured at Output Trace = 4 Inches

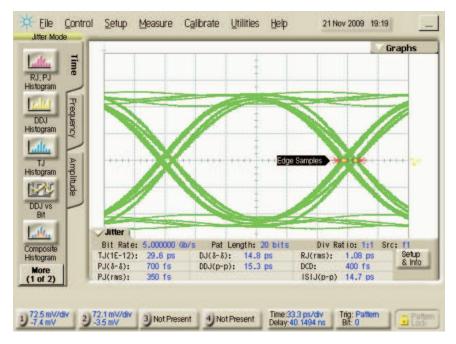


Figure 15. Input Trace = 44 Inches, 6 mil, and Measured at Output Trace = 4 Inches



Variable Trace Lengths at Input and Output

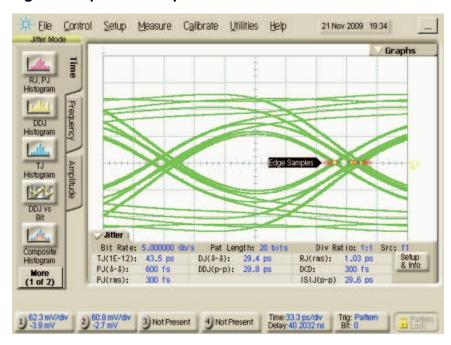


Figure 16. Input Trace = 28 Inches, 6 mil, and Measured at Output Trace = 24 Inches

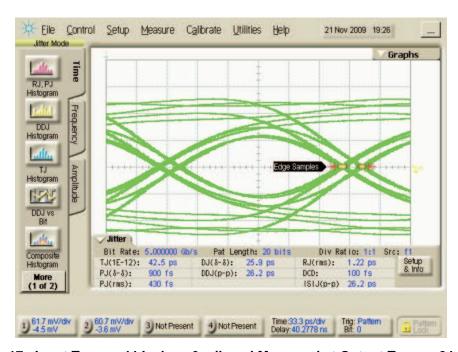


Figure 17. Input Trace = 44 Inches, 6 mil, and Measured at Output Trace = 24 Inches





REVISION HISTORY

Ch	hanges from Original (May 2010) to Revision A	Page
•	Added Figure 4	7





11-May-2012

PACKAGING INFORMATION

Orderable Device	Status		Package Pins Package Qty Drawing		Package Qty	Eco Plan ⁽²⁾ Lead/ Ball Finish		MSL Peak Temp ⁽³⁾	Samples (Requires Login)
SN65LVPE501RGER	ACTIVE	VQFN	RGE	24	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	
SN65LVPE501RGET	ACTIVE	VQFN	RGE	24	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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PACKAGE MATERIALS INFORMATION

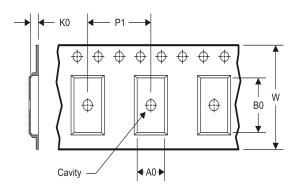
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TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

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	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	SN65LVPE501RGER	VQFN	RGE	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
	SN65LVPE501RGET	VQFN	RGE	24	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVPE501RGER	VQFN	RGE	24	3000	346.0	346.0	29.0
SN65LVPE501RGET	VQFN	RGE	24	250	210.0	185.0	35.0



- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
 - B. This drawing is subject to change without notice.
 - C. Quad Flatpack, No-Leads (QFN) package configuration.
 - D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
 - F. Falls within JEDEC MO-220.



RGE (S-PVQFN-N24)

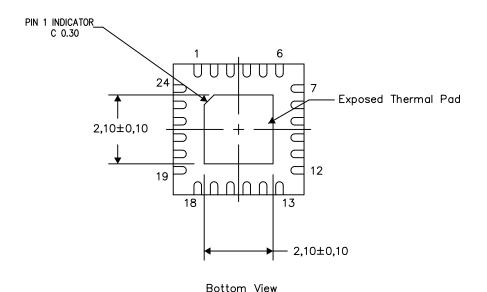
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

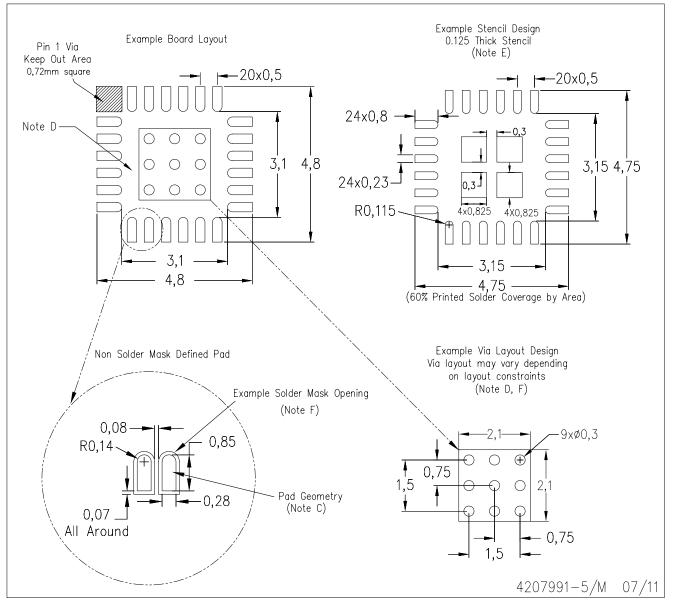
4206344-6/AA 04/12

NOTES: A. All linear dimensions are in millimeters



RGE (S-PVQFN-N24)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

- S: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com www.ti.com.
 - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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